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#### October 2013

# FGA60N65SMD 650 V, 60 A Field Stop IGBT

### Features

- Maximum Junction Temperature : T<sub>J</sub> = 175<sup>o</sup>C
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(sat)} = 1.9 V(Typ.) @ I_{C} = 60 A$
- Fast Switching : E<sub>OFF</sub> = 7.5 uJ/A
- Tighten Parameter Distribution
- RoHS Compliant

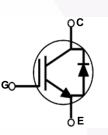
## Applications

• Solar Inverter, UPS, Welder, PFC, Telecom, ESS

# **General Description**

Using novel field stop IGBT technology, Fairchild's new series of field stop 2<sup>nd</sup> generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.





#### **Absolute Maximum Ratings**

| Symbol              | Description  |  | Ratings     | Unit |
|---------------------|--|--|-------------|------|
| V <sub>CES</sub>    | Collector to Emitter Voltage   |  | 650         | V    |
| V <sub>GES</sub>    | Gate to Emitter Voltage  |  | ± 20        | V    |
| GES                 | Transient Gate to Emitter Voltage  |  | ± 30        | V    |
| I <sub>C</sub>      | Collector Current  | @ T <sub>C</sub> = 25°C                              | 120         | A    |
|                     | Collector Current  | Collector Current @ $T_{\rm C} = 100^{\circ}{\rm C}$ |             | A    |
| I <sub>CM (1)</sub> | Pulsed Collector Current   |  | 180         | А    |
| I <sub>F</sub>      | Diode Forward Current  | @ T <sub>C</sub> = 25 <sup>o</sup> C                 | 60          | А    |
|                     | Diode Forward Current  | @ T <sub>C</sub> = 100°C                             | 30          | А    |
| I <sub>FM (1)</sub> | Pulsed Diode Maximum Forward Current                                       |  | 180         | А    |
| P <sub>D</sub>      | Maximum Power Dissipation  | @ T <sub>C</sub> = 25°C                              | 600         | W    |
| · D                 | Maximum Power Dissipation $@T_{C} = 100^{\circ}C$                          |  | 300         | W    |
| TJ                  | Operating Junction Temperature   |  | -55 to +175 | °C   |
| T <sub>stg</sub>    | Storage Temperature Range  |  | -55 to +175 | °C   |
| TL                  | Maximum Lead Temp. for soldering<br>Purposes, 1/8" from case for 5 seconds |  | 300         | °C   |

Notes:

1: Repetitive rating: Pulse width limited by max. junction temperature

# Thermal Characteristics

| Symbol                  | Parameter                               | Тур. | Max. | Unit |
|-------------------------|---|------|------|------|
| $R_{\theta JC}$ (IGBT)  | Thermal Resistance, Junction to Case    | -    | 0.25 | °C/W |
| $R_{\theta JC}$ (Diode) | Thermal Resistance, Junction to Case    | -    | 1.1  | °C/W |
| $R_{\thetaJA}$          | Thermal Resistance, Junction to Ambient | -    | 40   | °C/W |

# Package Marking and Ordering Information

| Device Marking | Device      | Package | Reel Size | Tape Width | Quantity |
|----------------|-------------|---------|-----------|------------|----------|
| FGA60N65SMD    | FGA60N65SMD | TO-3PN  | -         | -          | 30       |

# Electrical Characteristics of the IGBT $T_{C} = 25^{\circ}C$ unless otherwise noted

| Symbol                                 | Parameter                                    | Test Conditions  | Min. | Тур. | Max. | Unit |
|--|--|--|------|------|------|------|
|  | 4  |  |      |      |      |      |
| Off Charac                             |  | N/ 01/1 050 A  | 050  | r    |      | .,   |
| BV <sub>CES</sub>                      | Collector to Emitter Breakdown Voltage       | $V_{GE} = 0V, I_{C} = 250\mu A$                                      | 650  | -    | -    | V    |
| $\frac{\Delta BV_{CES}}{\Delta T_{J}}$ | Temperature Coefficient of Breakdown Voltage | $V_{GE} = 0V, I_C = 250\mu A$  | -    | 0.6  | -    | V/ºC |
| I <sub>CES</sub>                       | Collector Cut-Off Current                    | $V_{CE} = V_{CES}, V_{GE} = 0V$                                      | -    | -    | 250  | μΑ   |
| I <sub>GES</sub>                       | G-E Leakage Current                          | $V_{GE} = V_{GES}, V_{CE} = 0V$                                      | -    | -    | ±400 | nA   |
| On Charac                              | teristics                                    |  |      |      |      |      |
| V <sub>GE(th)</sub>                    | G-E Threshold Voltage                        | I <sub>C</sub> = 250μA, V <sub>CE</sub> = V <sub>GE</sub>            | 3.5  | 4.5  | 6.0  | V    |
| 0 = ()                                 |  | $I_{\rm C} = 60$ A, $V_{\rm GE} = 15$ V                              | -    | 1.9  | 2.5  | V    |
| V <sub>CE(sat)</sub>                   | Collector to Emitter Saturation Voltage      | $I_{C} = 60A, V_{GE} = 15V,$<br>$T_{C} = 175^{\circ}C$               | -    | 2.1  | -    | V    |
| Dynamic C                              | Characteristics                              |  |      |      |      |      |
| C <sub>ies</sub>                       | Input Capacitance                            |  | -    | 2915 | -    | pF   |
| C <sub>oes</sub>                       | Output Capacitance                           | V <sub>CE</sub> = 30V <sub>,</sub> V <sub>GE</sub> = 0V,<br>f = 1MHz | -    | 270  | -    | pF   |
| C <sub>res</sub>                       | Reverse Transfer Capacitance                 | T = TMHZ   | -    | 85   | -    | pF   |
| Switching                              | Characteristics                              |  |      |      |      |      |
| t <sub>d(on)</sub>                     | Turn-On Delay Time                           |  | -    | 18   | 27   | ns   |
| t <sub>r</sub>                         | Rise Time                                    |  | -    | 47   | 70   | ns   |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time                          | V <sub>CC</sub> = 400V, I <sub>C</sub> = 60A,                        | -    | 104  | 146  | ns   |
| t <sub>f</sub>                         | Fall Time                                    | $R_{G} = 3\Omega, V_{GE} = 15V,$                                     | -    | 50   | 68   | ns   |
| Eon                                    | Turn-On Switching Loss                       | Inductive Load, $T_C = 25^{\circ}C$                                  | -    | 1.54 | 2.31 | mJ   |
| E <sub>off</sub>                       | Turn-Off Switching Loss                      |  | -    | 0.45 | 0.60 | mJ   |
| E <sub>ts</sub>                        | Total Switching Loss                         |  | -    | 1.99 | 2.91 | mJ   |
| t <sub>d(on)</sub>                     | Turn-On Delay Time                           |  | - /  | 18   | -    | ns   |
| t <sub>r</sub>                         | Rise Time                                    |  | -    | 41   | -    | ns   |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time                          | V <sub>CC</sub> = 400V, I <sub>C</sub> = 60A,                        | -    | 115  | -    | ns   |
| t <sub>f</sub>                         | Fall Time                                    | $R_{G} = 3\Omega, V_{GE} = 15V,$                                     | -    | 48   | -    | ns   |
| E <sub>on</sub>                        | Turn-On Switching Loss                       | Inductive Load, T <sub>C</sub> = 175°C                               | -    | 2.08 | -    | mJ   |
| E <sub>off</sub>                       | Turn-Off Switching Loss                      |  | -    | 0.78 | -    | mJ   |
| E <sub>ts</sub>                        | Total Switching Loss                         | 1  | -    | 2.86 | -    | mJ   |

# Electrical Characteristics of the IGBT (Continued)

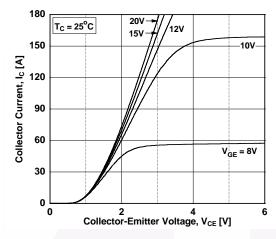
| Symbol          | Parameter                | Test Conditions  | Min. | Тур. | Max | Unit |
|-----------------|--------------------------|--|------|------|-----|------|
| Qg              | Total Gate Charge        |  | -    | 189  | 284 | nC   |
| Q <sub>ge</sub> | Gate to Emitter Charge   | V <sub>CE</sub> = 400V, I <sub>C</sub> = 60A,<br>V <sub>GE</sub> = 15V | -    | 20   | 30  | nC   |
| Q <sub>gc</sub> | Gate to Collector Charge | VGE - 10V  | -    | 91   | 137 | nC   |

# Electrical Characteristics of the Diode T<sub>C</sub> = 25°C unless otherwise noted

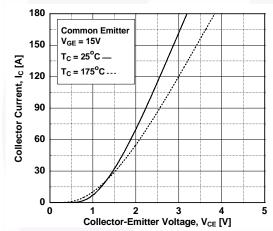
| Symbol                      | Parameter                                     | Test Conditions                                       |                                     | Min. | Тур. | Max | Unit |
|-----------------------------|---|---|-------------------------------------|------|------|-----|------|
| V <sub>FM</sub>             | Diode Forward Voltage                         | I <sub>F</sub> = 30A                                  | $T_{\rm C} = 25^{\rm o}{\rm C}$     | -    | 2.1  | 2.6 | V    |
| VFM Diode i of ward voltage |   |   | T <sub>C</sub> = 175°C              | -    | 1.7  | -   |      |
| E <sub>rec</sub>            | Reverse Recovery Energy                       |   | T <sub>C</sub> = 175 <sup>o</sup> C | -    | 127  | -   | uJ   |
| t <sub>rr</sub>             | Diode Reverse Recovery Time                   | I <sub>F</sub> =30A,<br>dI <sub>F</sub> /dt = 200A/μs | $T_{\rm C} = 25^{\rm o}{\rm C}$     | -    | 47   | -   | ns   |
| rr                          |   |   | T <sub>C</sub> = 175 <sup>o</sup> C | -    | 212  | -   | 110  |
| 0                           | Q <sub>rr</sub> Diode Reverse Recovery Charge |   | $T_{\rm C} = 25^{\rm o}{\rm C}$     | -    | 87   | -   | nC   |
| αn                          |   |   | T <sub>C</sub> = 175 <sup>o</sup> C | -    | 933  | -   | 110  |

# **Typical Performance Characteristics**











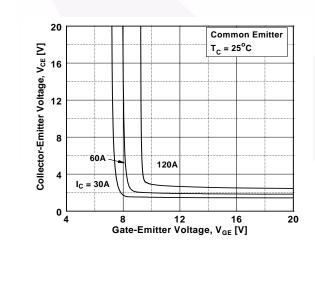


Figure 2. Typical Output Characteristics

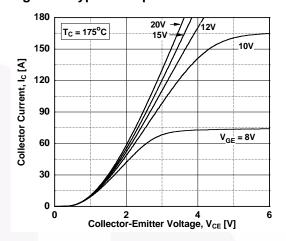
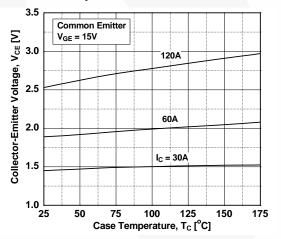
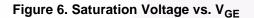
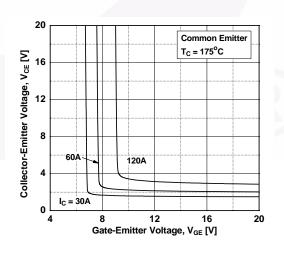


Figure 4. Saturation Voltage vs. Case Temperature at Variant Current Level

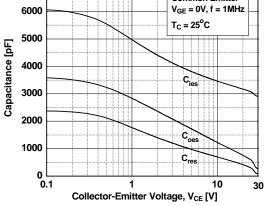






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# Typical Performance Characteristics Figure 7. Capacitance Characteristics 7000 Common Emitter Yung OV for 1000





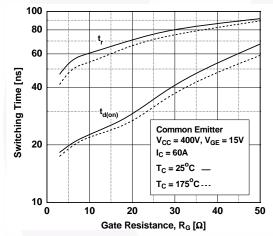


Figure 11. Switching Loss vs. Gate Resistance

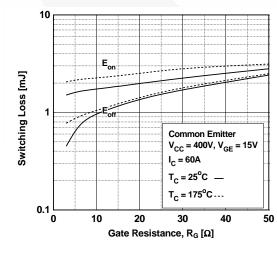
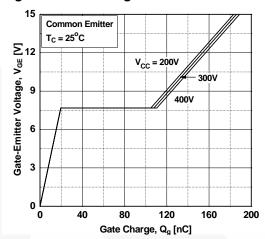
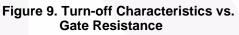
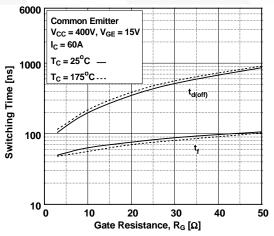
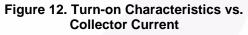


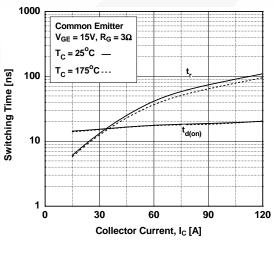
Figure 8. Gate charge Characteristics







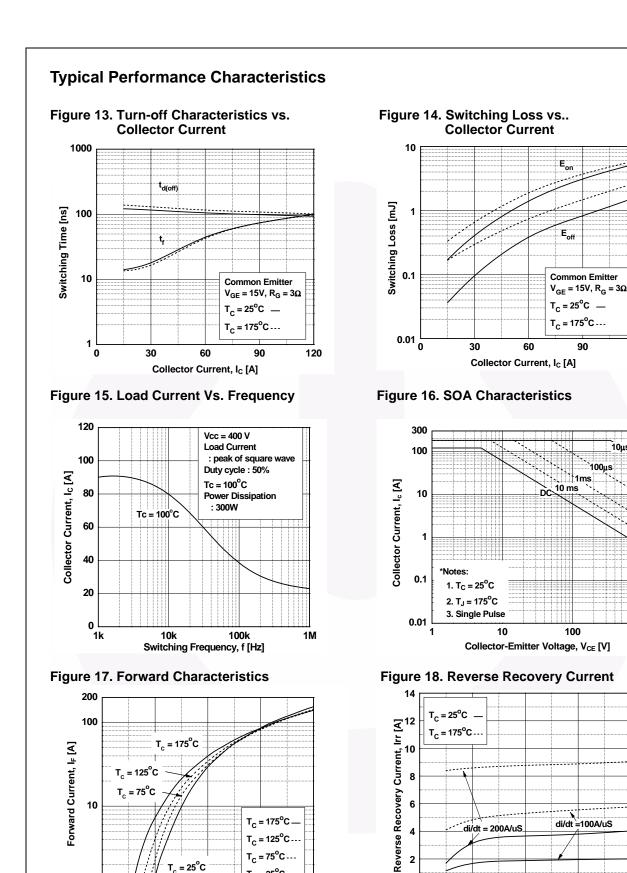




120

10µs

1000



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1

0

1

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40

6

0 ∟ 0

10

20

Forward Current, I<sub>F</sub> [A]

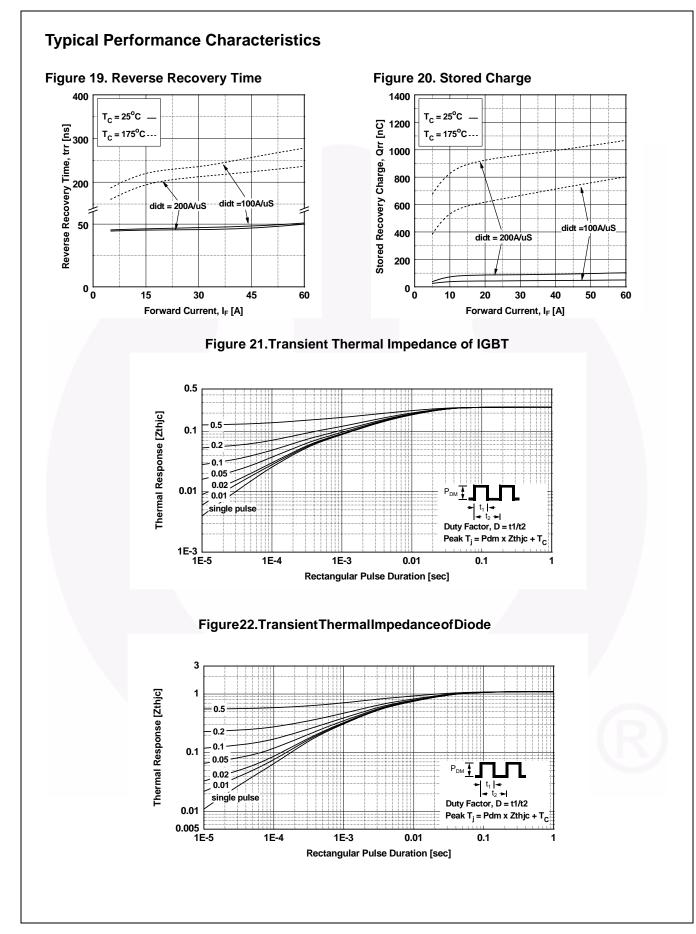
30

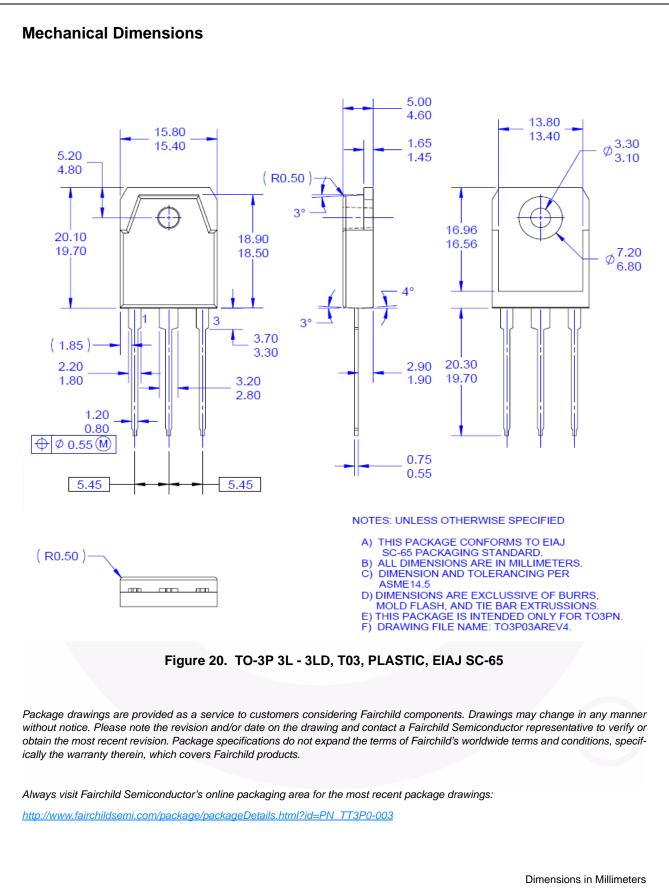
T<sub>C</sub> = 25°C

3

2

Forward Voltage, V<sub>F</sub> [V]





8



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